

International IR Rectifier

RADIATION HARDENED POWER MOSFET THRU-HOLE (Low-Ohmic TO-254AA)

PD - 94723

IRHMS67160 100V, N-CHANNEL R₆ TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	Id
IRHMS67160	100K Rads (Si)	0.011Ω	45A*
IRHMS63160	300K Rads (Si)	0.011Ω	45A*
IRHMS64160	600K Rads (Si)	0.011Ω	45A*
IRHMS68160	1000K Rads (Si)	0.011Ω	45A*



International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm²).

Their combination of very low RDS(on) and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low RDS(on)
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Electrically Isolated
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
ID @ VGS = 12V, TC = 25°C	Continuous Drain Current	45*	A
ID @ VGS = 12V, TC = 100°C	Continuous Drain Current	45*	
IDM	Pulsed Drain Current ①	180	
PD @ TC = 25°C	Max. Power Dissipation	208	W
	Linear Derating Factor	1.67	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	566	mJ
IAR	Avalanche Current ①	45	A
EAR	Repetitive Avalanche Energy ①	20.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	g

* Current is limited by package

For footnotes refer to the last page

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Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
B _V DSS	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔB _V DSS/ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.12	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.011	Ω	V _{GS} = 12V, I _D = 45A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	45	—	—	S (S)	V _{DS} = 25V, I _{DS} = 45A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 80V, V _{GS} = 0V
		—	—	25		V _{DS} = 80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	165	nC	V _{GS} = 12V, I _D = 45A
Q _{gs}	Gate-to-Source Charge	—	—	80		V _{DS} = 50V
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	60		
t _{d(on)}	Turn-On Delay Time	—	—	35	ns	V _{DD} = 50V, I _D = 45A
t _r	Rise Time	—	—	125		V _{GS} = 12V, R _G = 2.35Ω
t _{d(off)}	Turn-Off Delay Time	—	—	75		
t _f	Fall Time	—	—	20		
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm /0.25in. from package) to Source lead (6mm /0.25in. from package) with Source wires internally bonded from Source Pin to Drain Pad
C _{iss}	Input Capacitance	—	8877	—	pF	V _{GS} = 0V, V _{DS} = 25V
C _{oss}	Output Capacitance	—	1600	—		f = 100KHz
C _{rss}	Reverse Transfer Capacitance	—	20.5	—		
R _g	Internal Gate Resistance	—	1.05	—	Ω	f = 0.71MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	45*	A	
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	180		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _j = 25°C, I _S = 45A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	500	ns	T _j = 25°C, I _F = 45A, di/dt ≤ 100A/μs
Q _{RR}	Reverse Recovery Charge	—	—	6.4	μC	V _{DD} ≤ 25V ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

* Current is limited by package

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	0.60	°C/W	
R _{thCS}	Case-to-Sink	—	0.21	—		
R _{thJA}	Junction-to-Ambient	—	—	48		Typical socket mount

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

Radiation Characteristics

IRHMS67160

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Parameter	Description	Up to 600K Rads(Si) ¹		1000K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	100	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0	1.5	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	—	25	μA	V _{DS} = 80V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source On-State Resistance (TO-3)	—	0.011	—	0.011	Ω	V _{GS} = 12V, I _D = 45A
R _{DS(on)}	Static Drain-to-Source On-State Resistance (Low-Ohmic TO-254)	—	0.011	—	0.011	Ω	V _{GS} = 12V, I _D = 45A
V _{SD}	Diode Forward Voltage ④	—	1.2	—	1.2	V	V _{GS} = 0V, I _S = 45A

1. Part numbers IRHMS67160, IRHMS63160 and IRHMS64160

2. Part number IRHMS68160

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{DS} (V)						
				@ V _{GS} = 0V	@ V _{GS} = -5V	@ V _{GS} = -10V	@ V _{GS} = -15V	@ V _{GS} = -17V	@ V _{GS} = -19V	@ V _{GS} = -20V
Br	36.7	309	39.5	100	100	100	100	100	100	40
I	59.8	341	32.5	100	100	100	30	-	-	-
Au	82.3	350	28.4	100	100	-	-	-	-	-

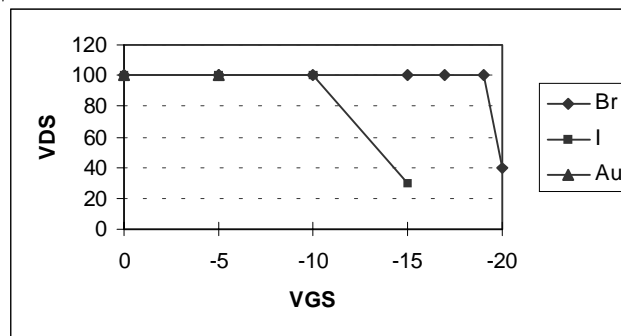


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

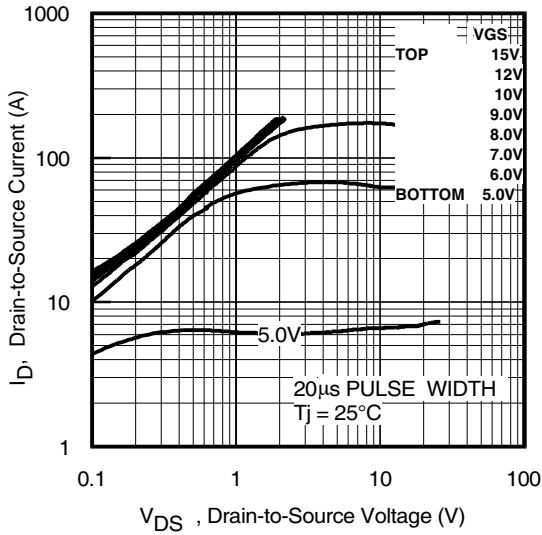


Fig 1. Typical Output Characteristics

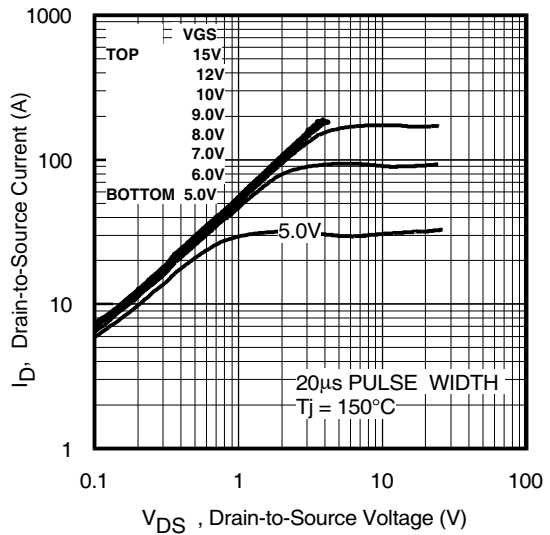


Fig 2. Typical Output Characteristics

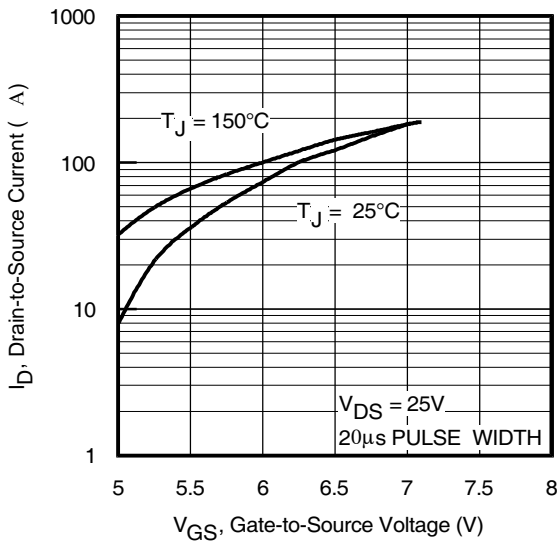


Fig 3. Typical Transfer Characteristics

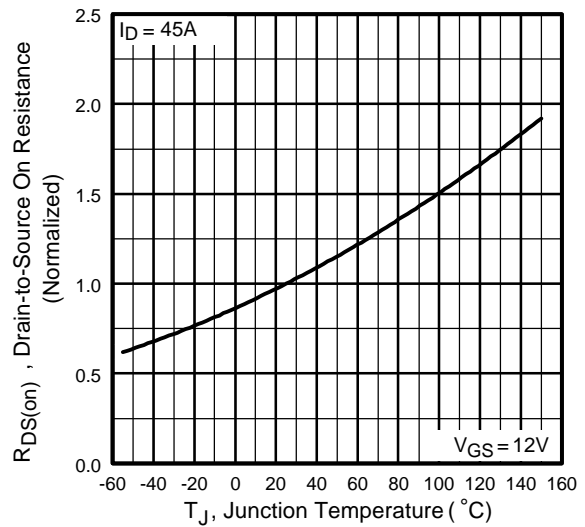


Fig 4. Normalized On-Resistance Vs. Temperature

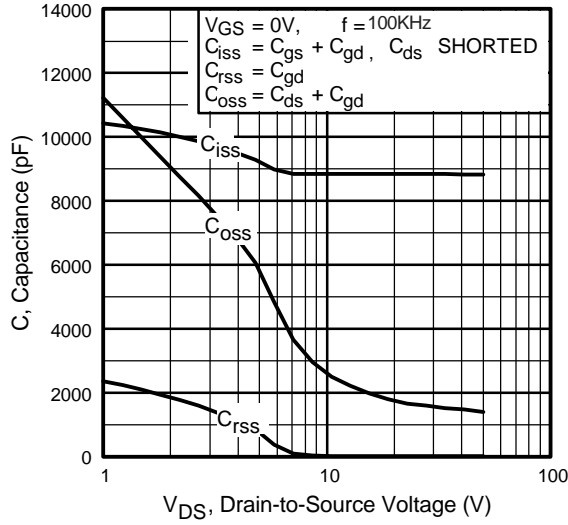


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

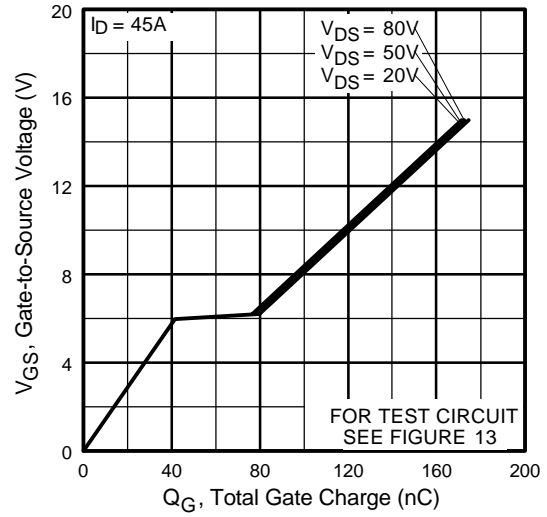


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

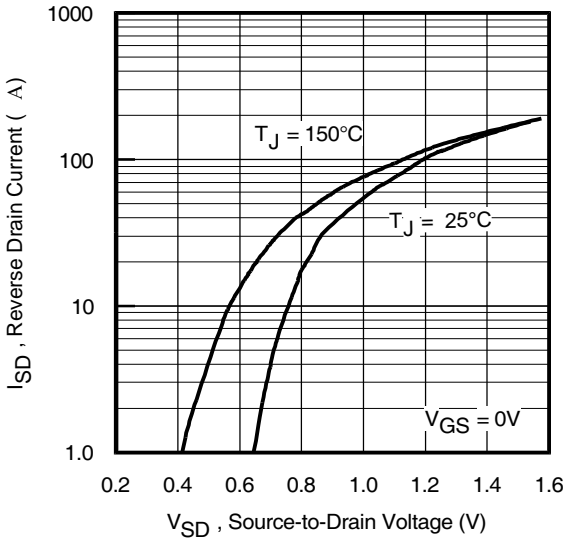


Fig 7. Typical Source-Drain Diode Forward Voltage

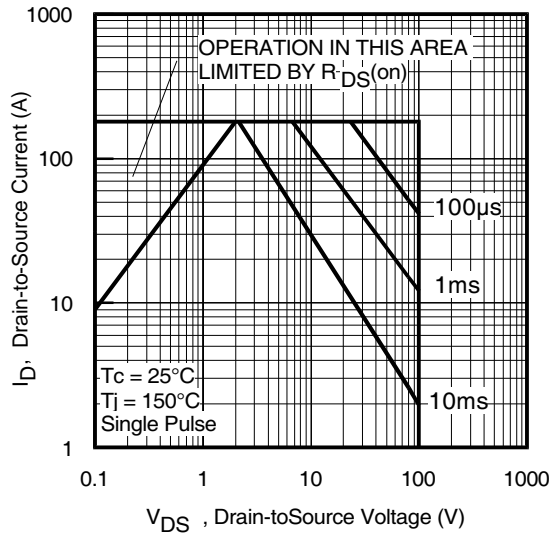


Fig 8. Maximum Safe Operating Area

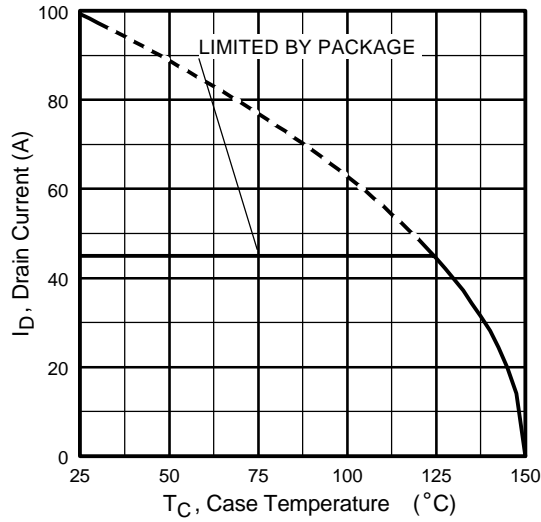


Fig 9. Maximum Drain Current Vs. Case Temperature

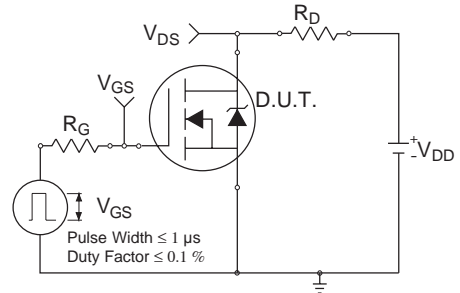


Fig 10a. Switching Time Test Circuit

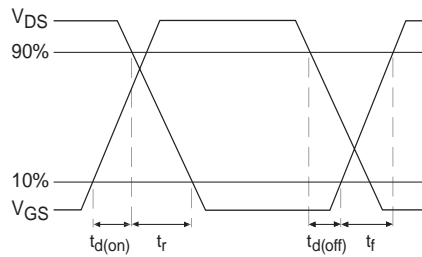


Fig 10b. Switching Time Waveforms

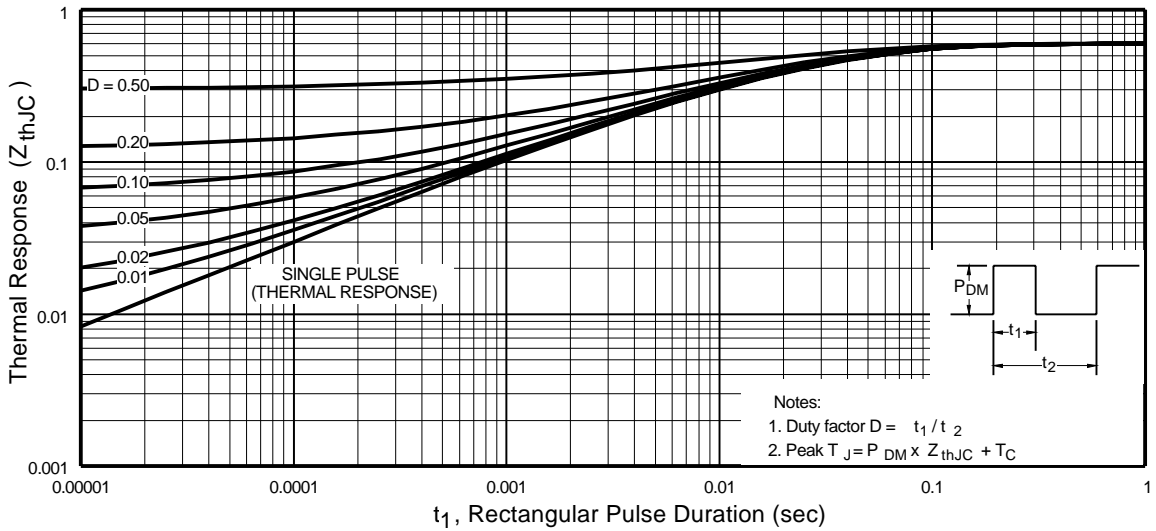


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

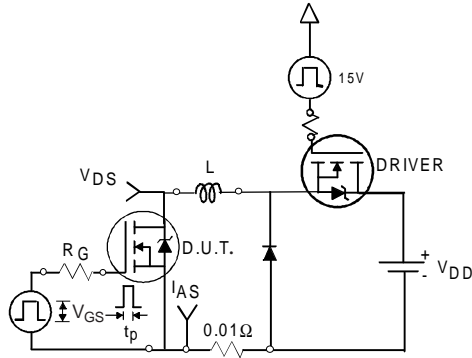


Fig 12a. Unclamped Inductive Test Circuit

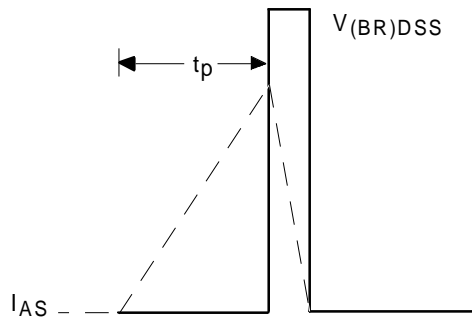


Fig 12b. Unclamped Inductive Waveforms

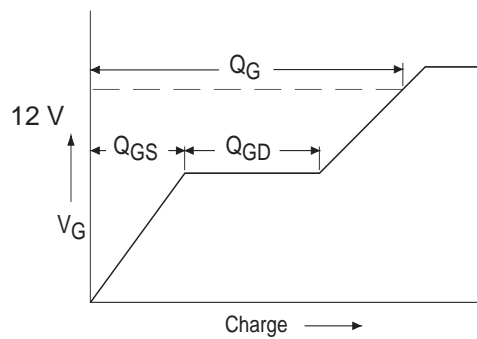


Fig 13a. Basic Gate Charge Waveform

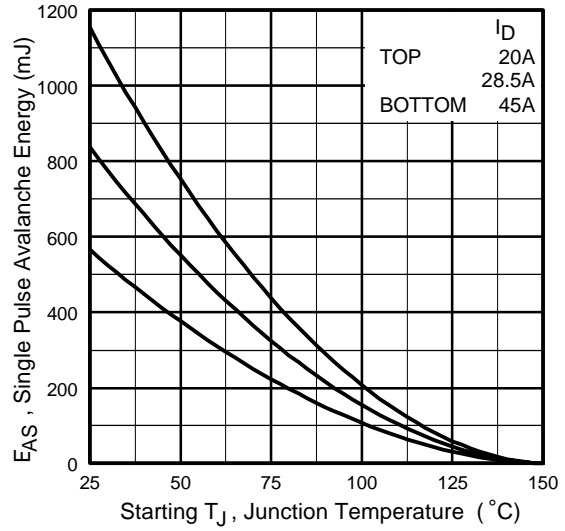


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

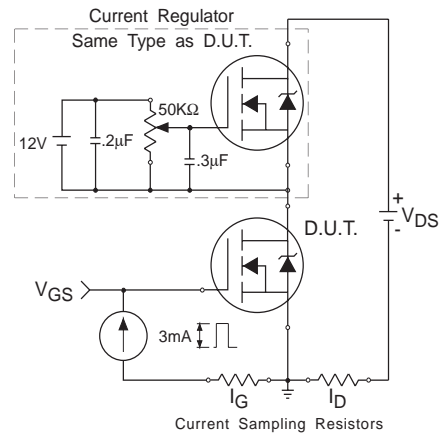
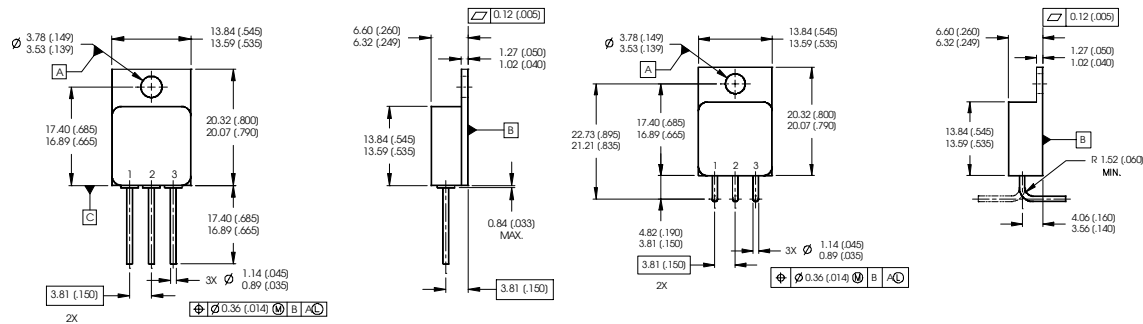


Fig 13b. Gate Charge Test Circuit

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ C$, $L = 0.56\text{ mH}$
Peak $I_L = 45A$, $V_{GS} = 12V$
- ③ $ISD \leq 45A$, $di/dt \leq 430A/\mu s$,
 $V_{DD} \leq 100V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300\ \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
80 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions —Low-Ohmic TO-254AA



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 3. CONTROLLING DIMENSION: INCH.
- 4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International
IR Rectifier

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Data and specifications subject to change without notice. 08/03



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